

Year	Author	Title	Journal
2000	G. Mueller	Growth of single crystals with high perfection	Proceedings of the Merton C. Flemings Symposium on Solidification and Materials Processing (2000), pp. 451-457
2000	D. Wolf, G. Müller	Kinetics of CIS formation studied in-situ by thin film calorimetry	Thin Solid Films, Volumes 361-362, 21 February 2000, pp. 155-160
2000	D. Vizman, I. Nicoara, G. Muller	Effects of temperature asymmetry and tilting in the vertical Bridgman growth of semi-transparent crystals	Journal-of-Crystal-Growth. Vol. 212, No. 1-2; April 2000; pp. 334-339
2000	A. Voigt, M. Metzger	Numerical Simulation and Control of Industrial Crystal Growth by the Czochralski and Vertical Gradient Freeze Method	caesar preprint 2000-2, (2000)
2000	D. Vizman, J. Friedrich, G. Müller	Three dimensional numerical simulation of thermal convection in a Czochralski melt	B. Sunden and C.A. Brebbia (Editors), Advanced Computational Methods in Heat Transfer VI, (2000), pp. 137-146
2000	D. Vizman, B. Fischer, J. Friedrich, G. Müller	3D numerical simulation of melt flow in the presence of a rotating magnetic field	Int. J. Num. Meth. Heat Fluid Flow 10, (2000), p. 366
2000	I. Nicoara, D. Vizman, J. Friedrich	On void engulfment in shaped sapphire crystals using 3D modelling	Journal of Crystal Growth, Volume 218, (2000), pp. 74-80
2000	G. Mueller, P. Berwian, E. Buhrig, B. Weinert	GaAs Substrate for high power laser diodes	in R. Diehl (Ed.), High Power Diode Lasers, Topics. Appl. Phys. 78, Springer, (2000), pp. 121-171
2000	A. Muehe, G. Mueller	Quantitative optical in-situ measurement of the dissolution rate of the silica crucible in the silicon Czochralski process	Materials Science in Semiconductor Processing, Volume 3, Issue 3, June 2000, pp. 185-189
2000	M. Metzger, R. Backofen	Optimal temperature profiles for annealing of GaAs-Crystals	Journal of Crystal Growth 220, (2000), pp. 6-15
2000	M. Kurz, G. Müller	Control of Thermal Conditions during Crystal Growth by Inverse Modelling	J. Cryst. Growth, 208, (2000), pp. 341-349
2000	C. Hack, G. Mueller	Nucleation of CIS thin films on monocrystalline CIS-substrates	EPSEC Glasgow, (2000)
2000	O. Graebner, A. Muehe, G. Mueller, E. Tomzig, J. Virbulis, W. von Ammon	Analysis of turbulent flow in silicon melts by optical temperature measurement	Materials Science and Engineering B: Solid-State Materials for Advanced Technology, Volume 73, Issue 1, 2000, pp. 130-133
2000	J. Friedrich, B. Fischer, O. Gräbner, D. Vizman, G. Müller	High performance computing for the analysis of the influence of steady magnetic fields on convective heat transfer in Czochralski melts: comparison to experimental results	Proc. 4th Int. PAMIR Conference, Presqu'île de Giens, France, (2000), pp. 239-244
2000	Ch. Frank, K. Jacob, M. Neubert, P. Rudolph, J. Fainberg, G. Müller	Temperature field simulation and correlation to the structural quality of semi-insulating GaAs crystals grown by the vapour pressure controlled Czochralski method (VCz)	J. Cryst. Growth 213, (2000), pp. 10-18
2000	B. Fischer, J. Friedrich, U. Hilburger, G. Müller	Systematic study of buoyant flows in vertical melt cylinders under the influence of rotating magnetic fields	Proc. EPM2000, Nagoya, Japan, (2000), pp. 497-502
2000	B. Eisener, D. Wolf, G. Müller	Influence of Sulphur on the electrical and optical properties of p-type $\text{CuIn}(\text{SxSe}1-x)_2$ single crystals	Thin Sol. Films, 361, 2000, pp. 126-129

2000	B. Birkmann, M. Rasp, J. Stenzenberger, G. Mueller	Growth of 3 " and 4 " gallium arsenide crystals by the vertical gradient freeze (VGF) method	Journal of Crystal Growth, Volume 211, Issue 1, 2000, pp. 157-162
2000	P. Berwian, D. Wolf, G. Mueller, W. Stetter, F. Karg	Investigation of phase transformation in the Cu-In-Ga-Se-system by thin film calorimetry and x-ray diffraction	EPSEC Glasgow, (2000)
2000	R. Backofen, M. Kurz, G. Müller	Process Modelling of the Industrial VGF Crystal Growth Process Using the Software Package CrysVUN++	J. Cryst. Growth 211, (2000), pp. 202-206
1999	G. Müller, A. Mühe, R. Backofen, E. Tomzig, W. v. Ammon	Study of Oxygen transport in Cz growth of silicon	Microelectronics Engineering 1, (1999), pp. 135-147
1999	A. Mühe, R. Backofen, J. Fainberg, G. Müller, E. Dornberger, E. Tomzig, W. v. Ammon	Oxygen Distribution in Silicon Melt During a Standard Czochralski Process Studied by Sensor Measurements and Comparison to Numerical Simulation	J. Crystal Growth 198/199, (1999)
1999	M. Metzger	Existence for a Time-dependent Heat Equation with Non-local Radiation Terms	Math.Meth.Appl.Sci. 22, (1999), pp. 1101-1119
1999	M. Leicht, D. Stenkamp, H.P. Strunk, D. Wolf, B. Eisener, G. Müller	Nanoscopic crystallography of chalcopyrite CuInS ₂ by techniques of convergent-beam electron diffraction	Phil Mag. A79, (1999), pp. 1033-1043
1999	M. Kurz, A. Pusztai, G. Müller	Development of a new powerful computer code CrysVUN++ especially designed for fast simulation of bulk crystal growth processes	J. Crystal Growth 198/199, (1999), pp. 101-106
1999	M. Kurz, J. Fainberg, J. Friedrich, G. Mueller	Equipment and process modelling of industrial crystal growth using the finite volume codes CrysVUN++ and STHAMAS	American Society of Mechanical Engineers, Pressure Vessels and Piping Division (Publication) PVP, Volume 397, (1999), pp. 275-281
1999	J. Friedrich, G. Müller	The influence of steady and alternating magnetic fields in crystal growth and alloy solidification: Industrial importance, current industrial R&D topics, links to microgravity research	ESA SP 433, (1999), pp. 309-314
1999	J. Friedrich, G. Müller	The use of magnetic fields in crystal growth and alloy solidification: Importance for industrial technologies and for microgravity research	Low G Journal 1, (1999), pp. 11-12
1999	J. Friedrich, Y. Lee, B. Fischer, C. Kupfer, D. Vizman, G. Müller	Experimental and numerical study of Rayleigh-Benard convection affected by a rotating magnetic field	Physics of Fluids 11, (1999), pp. 853-861
1999	B. Fischer, G. Wellein, G. Müller	3D time-dependent numerical simulation of buoyant convection in vertical melt cylinders under the influence of rotating magnetic fields	in Annual Report LRZ Munic, (1999)
1999	B. Fischer, U. Hilburger, J. Friedrich, G. Müller	Temperature and velocity analysis in vertical melt cylinders under the influence of rotating magnetic fields and buoyant convection	Proc. MTLM Workshop, Rossendorf, (1999)
1999	B. Fischer, J. Friedrich, H. Weimann, G. Müller	The use of time-dependent magnetic fields for control of convective flows in melt growth configurations	J. Crystal Growth 198/199, (1999), pp. 170-175
1999	B. Fischer, J. Friedrich, C. Kupfer, G. Müller, D. Vizman	Experimental and numerical analysis of the influence of a rotating magnetic field on convection in Rayleigh Benard configurations	in Transfer Phenomena in Magnetohydrodynamics and Electroconducting Flows, Kluwer, Dordrecht, (1999), pp. 279-294
1999	B. Eisener, M. Wagner, D. Wolf, G. Müller	Study of the intrinsic defects in solution grown CuInSe ₂ crystals depending on the path of crystallization	J. Crystal Growth 198/199, (1999), pp. 321-324

1999	K. Bottcher, P. Rudolph, M. Neubert, M. Kurz, A. Pusztai, G. Müller	Global temperature field simulation of the vapour pressure controlled Czochralski (VCZ) growth of 3"-4" gallium arsenide crystals	Journal-of-Crystal-Growth, Vol. 198-199, Pt.1, March 1999, pp. 349-354
1999	J. Amon, J. Härtwig, W. Ludwig, G. Müller	Analysis of Types of Residual Dislocations in the VGF Growth of GaAs with extremely low Dislocation Density (EPD << 1000cm ⁻²)	J. Crystal Growth, (1999), pp. 367-373
1999	J. Amon, P. Berwian, G. Müller	Computer-Assisted Growth of Low-EPD GaAs with 3" Diameter by the Vertical Gradient-Freeze Technique	J. Crystal Growth 198/199, (1999), pp. 361-366
1998	D. Wolf, G. Müller	In-situ Investigation of Cu-In-Se-Reactions by Thin-Film Calorimetry	Thin-Film, Structures for Photovoltaics. Symposium. Materials Research Society, Warrendale, PA, USA, (1998), pp. 173-178
1998	D. Wolf, G. Müller, W. Stetter, F. Karg	In-situ Investigation of Cu-In-Se Reactions: Impact of Na on CIS Formation	2nd Conf. on PV Sol. Energy Conv., Vienna, Austria, (1998), pp. 2426-2430
1998	D. Wolf, G. Müller	Thin Film Calorimetry as a Tool for in-situ Investigation of Reactions in the Cu-In-Se ternary System	Ternary and Multinary Compounds. Proceedings of the 11th International Conference on Ternary and Multinary Compounds. ICTMC-11. Institute of Physics Publishing, Bristol, UK, (1998), pp. 281-284
1998	A. Seidl, G. Müller, E. Dornberger, E. Tomzig, B. Rexer, W. v. Ammon	Turbulent melt convection and its implication on large diameter silicon Czochralski crystal growth	Proceedings of the Eighth International Symposium on Silicon Materials Science and Technology. Silicon Materials Science and Technology. Electrochem. Soc, Pennington, NJ, USA, (1998), pp. 417-428
1998	G. Müller	Melt Growth of Semiconductors	Materials-Science-Forum. Vol. 276-277, 1998, pp. 87-108
1998	M. Kurz, A. Pusztai	Presentation of a gentle discretisation scheme for the numerical treatment of nonlinear heat conduction on unstructured grids in finite volume technique	Int. J. Num. Methods for Heat & Fluid Flow, Vol. 8, No. 3, (1998), p. 304
1998	Ch. Hack, D. Wolf, G. Müller	Liquid Phase Homoepitaxy of CuInS ₂	Ternary and Multinary Compounds. Proceedings of the 11th International Conference on Ternary and Multinary Compounds. ICTMC-11. Institute of Physics Publishing, Bristol, UK, (1998), pp. 285-288
1998	J. Friedrich, G. Müller	The Influence of Steady and Alternating Magnetic Fields on Crystal Growth and Alloy Solidification: Links to Microgravity	Annales of the European Academy of Sciences and Arts
1998	B. Eisener, H. Kuhn, G. Drüsslein, D. Wolf, G. Müller	Solution growth of CuInSe ₂ and CuInS ₂ bulk crystals and their characterization	Ternary and Multinary Compounds. Proceedings of the 11th International Conference on Ternary and Multinary Compounds. ICTMC-11. Institute of Physics Publishing, Bristol, UK, (1998), pp. 131-134
1998	J. Amon, F. Dumke, G. Müller	Influence of the crucible shape on the formation of facets and twins in the growth of GaAs by the vertical gradient freeze technique	J. Cryst. Growth 187, (1998), p. 1
1997	H. Weimann, J. Friedrich, D. Vizman, G. Müller	3D-Modelling of Marangoni-Convection in Floating-Zone Growth of GaAs under Microgravity and Rotating Magnetic Fields	Proc. of "Joint Xth European and Vth Russian Symposium on Physical Sciences in Microgravity", St. Petersburg, Russia, 15-21 June 1997, pp. 78-86
1997	H. Weimann, J. Amon, Th. Jung, G. Müller	Numerical simulation of the growth of 2" diameter GaAs crystals by the Vertical Gradient Freeze technique	J. Cryst. Growth 180, 1997, pp. 560-565
1997	T. Jung, G. Müller	Amplitudes of doping striations: comparison of numerical calculations and analytical approaches	J. Cryst. Growth 171, (1997), pp. 373-397
1997	A. Seidl, G. Müller	Oxygen solubility in silicon melt measured in-situ by an electrochemical solid ionic sensor	J. Electrochem. Soc. 144/9, (1997), pp. 3243-3245

1997	J. Friedrich, G. Müller	Use of magnetic fields and/or microgravity conditions to control convection during materials processing of semiconductors and metals	Low-g-Journal 8(2), (1997), pp. 10-11
1997	J. Fainberg, H.-J. Leister, G. Müller	Numerical simulation of the LEC-growth of the GaAs crystals with account of high pressure gas convection	J. Cryst. Growth 180, (1997), pp. 517-523
1997	J. Friedrich, C. Kupfer, B. Fischer, G. Müller	Influence of rotating magnetic fields on heat and species transport in crystal growth by the Vertical Gradient Freeze method	Proc. 3rd Int. Conf. on Transfer Phenomena in Magnetohydrodynamic & Electroconducting Flows, Aussois, France, 22-26 September 1997, pp. 439-444
1997	B. Fischer, J. Friedrich, C. Kupfer, D. Vizman, G. Müller	Experimental and numerical analysis of the influence of rotating magnetic fields on heat transport in Rayleigh Benard configurations	Proc. 3rd Int. Conf. on Transfer Phenomena in Magnetohydrodynamic & Electroconducting, Flows Aussois, France, 22-26 September 1997, pp. 337-342
1997	E. Dornberger, E. Tomzig, A. Seidl, S. Schmitt, H.-J. Leister, Ch. Schmitt, G. Müller	Thermal simulation of the Czochralski silicon Growth process by three different models and comparison with experimental results	J. Cryst. Growth 180, (1997), pp. 461-467
1996	G. Marrakchi, K. Cherkaoui, A. Karoui, G. Hirt, G. Müller	Traps in undoped semi-insulating InP obtained by high temperature annealing	Journal of Applied Physics 79 (9) (1996), pp. 6947-6950
1996	D. Zemke, H.J. Leister, G. Müller	Growth of InP Bulk Crystals by VGF: A Comparative Study of Dislocation Density and Numerical Stress Analysis	IPRM 1996. Eighth International Conference on Indium Phosphide and Related Materials (Cat.No.96CH35930). IEEE, New York, NY, USA, 1996, xiv+765, p. 47
1996	D. Wolf, R. Lerner, G. Müller	Study of the nucleation of CuInS ₂ on III-V substrates by liquid phase epitaxy	Cryst. Res. Technol. 31 Spec. Issue 1 (1996), pp. 317-320
1996	A. Seidl, R. Marten, G. Müller	Oxygen distribution in Czochralski silicon melts measured by an electrochemical oxygen sensor	Mat. Sci. Eng. B 36 (1996), pp. 46-49
1996	A. Seidl, R. Marten, G. Müller	In-situ investigation of oxygen distribution and transport in Czochralski silicon melts by electrochemical solid ionic sensors	J. Cryst. Growth 166 (1996), p. 680
1996	G. Müller, F.M. Herrmann	Growth of 20mm Diameter GaAs Crystals by the Floating Zone Technique During the D-2 Spacelab Mission	L. Ratke, H.U. Walter (eds.), "Materials and Fluids Under Low Gravity" (Lecture Notes in Physics) Springer-Berlin 1996, pp. 105-111
1996	M. Müller, G. Gärtner, M. Jurisch, A. Köhler, G. Müller, B. Weinert	Control of Oxygen in Undoped LEC-GaAs	J. Crystal Growth 166 (1996), pp. 636-640
1996	R. Lerner, D. Wolf, G. Müller	Crystal growth and characterization of CuInS ₂	Cryst. Res. Technol. 31 Spec. Issue 1 (1996), pp. 57-60
1996	T. Jung, G. Müller	Effective segregation coefficients: a comparison of axial solute distributions predicted by analytical boundary layer models and numerical calculations	J. Cryst. Growth 165 (1996), pp. 463-470
1996	G. Hirt, D. Wolf, B. Hoffmann, U. Kretzer, G. Kühnel, A. Woitech, D. Zemke, G. Müller	Mesoscopic nonuniformity of wafer-annealed semi-insulating InP	J. Electron. Mat. 25 (1996), pp. 363-367
1996	J. Friedrich, G. Müller	Convection in crystal growth under high gravity on a centrifuge	Proc. of the 3rd Int. Conf. on Materials Processing under High Gravity, Plenum Press New York (1996), pp. 17-29
1996	J. Friedrich, G. Müller	Segregation in crystal growth under high gravity on a centrifuge. A comparison between experimental and theoretical results	Proc. of the 3rd Int. Conf. on Materials Processing under High Gravity, Plenum Press New York (1996), pp. 29-45

1996	J. Friedrich, H.-J. Leister, A. Seidl, G. Müller	Numerical 3D-simulation of the transport processes in semiconductor crystal growth	Overview of Research Projects on the Cray Y-Mp at the Leibniz-Rechenzentrum München, München (1996), pp. 125-129
1996	J. Friedrich, J. Baumgartl, H.-J. Leister, G. Müller	Experimental and theoretical analysis of convection and segregation in Vertical Bridgman growth under high gravity on a centrifuge	J. Cryst. Growth 167 (1996), pp. 45-63
1996	J. Fainberg, H.-J. Leister	Finite Volume multigrid solver for thermoelastic stress analysis in anisotropic materials	Comp. Meth. Appl. Mech. Eng. 137 (1996), pp. 167-174
1996	J. Baumgartl, G. Müller	The use of magnetic fields for damping the action of gravity fluctuations (g-jitter) during crystal growth under microgravity	J. Crystal Growth 169 (1996), pp. 582-586
1996	J. Amon, D. Zemke, B. Hofmann, G. Müller	Growth of 2'' InP and GaAs crystals by the Vertical Gradient Freeze (VGF) technique and characterization	J. Cryst. Growth 166 (1996), 646
1995	D. Wolf, G. Hirt, G. Müller	Control of low Fe content in the preparation of semi-insulating InP by wafer-annealing	J. Electron. Mat. 24 (1995), p. 93
1995	F. Herrmann, G. Müller	Growth of 20mm diameter GaAs crystals by the Floating Zone technique with controlled As-vapour pressure under microgravity	J. Cryst. Growth 156 (1995), p. 350
1995	G. Hirt, B. Hoffmann, U. Kretzer, A. Woitech, D. Zemke, G. Müller	Preparation of homogeneous InP substrates by VGF-growth and wafer annealing	Conference Proceedings. Seventh International Conference on Indium Phosphide and Related Materials (Cat. No.95CH35720). IEEE, New York, NY, USA, 1995, xiv+869, p. 33
1995	P. Gille, S. Scharl, G. Müller	A generalized description of solute distribution in melt growth by the Submerged Heater method	J. Cryst. Growth 148 (1995), p. 183
1994	D. Zemke, I. Grant, G. Wittmann, G. Müller	Growth and characterization of 2 in InP crystals by the vertical gradient freeze technique	Mat. Sci. Eng. B28 (1994), p. 91
1994	D. Wolf, G. Hirt, F. Mosel, G. Müller, J. Völkl	Preparation and characterization of semi-insulating 2''InP wafers having a low Fe content by wafer annealing	Mat. Sci. Eng. B28 (1994), p. 115
1994	J. Voelkl	Stress in cooling crystal	in D. Hurle (Ed.): Handbook of Crystal Growth Vol 2, Elsevier (1994), pp. 823-871
1994	A. Seidl, F. Mosel, G. Müller	Non-uniformity of Fe doping in semi-insulating LEC-grown InP and its characterization by various mapping methods	Mat. Sci. Eng. B28 (1994), p. 107
1994	A. Seidl, G. McCord, G. Müller, H.-J. Leister	Experimental observation and numerical simulation of wave patterns in a Czochralski silicon melt	J. Cryst. Growth 137 (1994), p. 326
1994	A. Seidl, R. Marten, G. Müller	Development of an electrochemical oxygen sensor for Czochralski silicon melts	J. Electrochem. Soc. 141 (1994), p. 2564
1994	A.G. Ostrogorsky, G. Müller	Normal and zone solidification using the Submerged Heater method	J. Cryst. Growth 137 (1994), p. 64
1994	G. Mueller, A.G. Ostrogorsky	Convection in melt growth	in D. Hurle (Ed.): Handbook of Crystal Growth Vol 2, Elsevier (1994), pp. 711-814

1994	G. Müller	Numerical simulation of crystal growth processes	Notes on Numerical Fluid Mechanics 48 (1994), p. 130
1994	K. Koai, A. Seidl, H.-J. Leister, G. Müller, A. Köhler	Modelling of thermal fluid flow in the liquid encapsulated Czochralski process and comparison with experiments	J. Cryst. Growth 137 (1994), p. 41
1994	K. Kainosho, O. Oda, G. Hirt, G. Müller	Semi-Insulating Behavior of Undoped InP	Materials Research Society Symposium Proceedings 325 (1994), pp. 101-112
1994	G. Hirt, D. Wolf, G. Müller	Diffusion mechanisms controlling the preparation of semi-insulating InP	Conf. on Semi-insulating III-V Materials 1994, Warsaw (Poland)
1994	G. Hirt, T. Mono, G. Müller	Spectroscopic investigation of deep levels related to the compensation mechanism of nominally undoped s.i. InP	Mat. Sci. Eng. B28 (1994), p. 101
1994	F. Herrmann, G. Müller	Growth of GaAs crystals by the Floating Zone technique during the D2 spacelab mission	Low G 5 (1994), p. 10
1993	T. Wolf, D. Drews, H. Scheffler, D. Bimberg, F. Mosel, P. Kipfer, G. Müller	Identification of deep levels in LEC-grown Fe- and Zn-doped InP: A proof of the nonexistence of a Fe ⁴⁺ /Fe ³⁺ donor level	J. Appl. Phys. 73 (1993), p. 226
1993	G. Wittmann, F. Mosel, G. Müller, A. Seidl, A. Winnacker	Investigation of the distribution of Fe in semi-insulating LEC-grown InP by photoluminescence and absorption imaging	Mat. Sci. Eng. B20 (1993), p. 91
1993	A. Seidl, F. Mosel, J. Friedrich, U. Kretzer, G. Müller	Optical cross sections and distribution of Fe ²⁺ and Fe ³⁺ in semi-insulating LEC-grown InP:Fe	Mat. Sci. Eng. B21 (1993), p. 321
1993	K. Rottner, R. Helbig, G. Müller	Piezoelectric constant of InP	Appl. Phys. Lett. 62 (1993), p. 352
1993	A.G. Ostrogorsky, H.J. Sell, S. Scharl, G. Müller	Convection and segregation during growth of Ge and InSb crystals by the Submerged Heater method	J. Cryst. Growth 128 (1993), p. 201
1993	A. Ostrogorsky, G. Mueller	Model of the effective segregation coefficient applied to low-convection solidification in microgravity	Journal-of-Crystal-Growth. Vol.128, No.1-4, March 1993, pp. 207-212
1993	G. Müller, D. Hofmann, N. Schäfer	Perspectives of the VGF Growth Process for the Preparation of Low-Defect InP Substrate Crystals	Conference Proceedings Fifth International Conference on Indium Phosphide and Related Materials. IEEE, New York, NY, USA, May 1993, xx+738, p. 60
1993	G. Müller	Convection instabilities in melt growth configurations	J. Cryst. Growth 128 (1993), p. 26
1993	D. Hofmann, T. Jung, G. Mueller	Growth of 2 inch Ge:Ga crystals by the dynamical vertical gradient freeze process and its numerical modelling including transient segregation	Journal-of-Crystal-Growth. Vol.128, No.1-4, March 1993, pp. 213-218
1993	D. Hofmann, T. Jung, N. Schäfer, D. Zemke, G. Müller	Model-based directional solidification of semiconductor materials by the VGF-technique using multi-zone cold wall furnace technology	Mater. Sci. Eng. A173 (1993), p. 67
1993	G. Hirt, D. Wolf, G. Müller	Quantitative study of the contribution of deep and shallow levels to the compensation mechanisms in annealed InP	J. Appl. Phys. 74 (1993), p. 5538

1993	G. Hirt, S. Bornhorst, J. Friedrich, N. Schäfer, G. Müller	Electronic properties of InP grown and annealed under controlled Phosphorus atmosphere	in Proc. of 5th Int. Conf. on InP and related Materials (1993), pp. 313-316
1993	J. Baumgartl, A. Hubert, G. Müller	The use of magnetohydrodynamic effects to investigate fluid flow in electrically conducting melts	Physics of Fluids A 5 (1993), p. 1
1993	J. Baumgartl, A. Bune, K. Koai, G. Müller, A. Seidl	Global simulation of heat transport, including melt convection in a Czochralski crystal growth process – combined finite element / finite volume approach.	Mat. Sci. Eng. A173 (1993), p. 913
1992	T. Wolf, D. Bimberg, G. Hirt, D. Hofmann, G. Mueller	A spectroscopic investigation of nominally undoped semi-insulating InP prepared by high temperature annealing	in Proc. of 4th Int. Conf. on InP and related Materials (1992), pp. 630-633
1992	A.G. Ostrogorsky, G. Müller	A model of effective segregation coefficient, accounting for convection in the solute layer at the growth interface	J. Cryst. Growth 121 (1992), p. 587
1992	G. Müller, G. Neumann, W. Weber	The growth of homogeneous semiconductor crystals in a centrifuge by the stabilizing influence of the Coriolis force	J. Cryst. Growth 119 (1992), p. 8
1992	G. Müller, G. Hirt, D. Hofmann	Current issues in bulk growth of s.i. III-V materials	7th Int. Conf. on Semi-insulating III-V Materials 1992, ed. by C.J. Miner et al., Inst. of Physics Publishing, Bristol 1992, p. 73
1992	W. Jantz, R. Stibal, J. Windscheif, F. Mosel, G. Müller	Nondestructive high resolution resistivity topography of semi-insulating GaAs and InP wafers	Semi-insulating III-V Materials 1992, ed. by C.J. Miner et al., Inst. of Physics Publishing, Bristol 1992, p. 171
1992	F.M. Herrmann, J. Baumgartl, T. Feulner, G. Müller	The Use of Magnetic Fields for Damping Unsteady Marangoni Convection in GaAs Floating Zones Under μ G	Proceedings VIIIth European Symposium on Materials and Fluid Science in Microgravity ESA SP-333 (1992), pp. 57-60
1992	J. Baumgartl, G. Müller	Calculation of the effects of magnetic field damping on fluid flow – Comparison of magnetohydrodynamic models of different complexity	Microgravity Quarterly 2 (1992), p. 197
1992	J. Baumgartl, G. Müller	Calculation of the Effects of magnetic Field Damping on Fluid Flow – Comparison of Magnetohydrodynamic Models of Different Complexity	Proceedings VIIIth European Symposium on Materials and Fluid Science in Microgravity ESA SP-333 (1992), pp. 161-164
1991	N. Schäfer, J. Stierlen, G. Müller	Growth of InP crystals by the Horizontal Gradient Freeze technique	Mat. Res. Eng. B9 (1991), p. 19
1991	R. Rupp, G. Müller	Experimental study of the surface tension of molten GaAs and its temperature dependence under controlled As-vapor pressure	J. Cryst. Growth 113 (1991), p. 131
1991	R. Rupp, F. Herrmann, G. Müller	Tiegefreies Zonenschmelzen von GaAs	Forschung unter Weltraumbedingungen, DARA Symposium (1991), pp. 97-106
1991	R. Rupp, S. Auerochs, G. Müller, C. Weyrich, S. Leibenzeder	Growth of GaAs single crystals by the Floating Zone Technique under microgravity	Adv. Space Res. 11 (1991), p. 297
1991	A. Ostrogorsky, F. Mosel, M. Schmidt	Diffusion-Controlled distribution in Sn-1%Bi specimens solidified by the submerged heater method	J. Crystal Growth 110 (1991), pp. 950-954
1991	G. Müller, R. Rupp	The role of Marangoni convection in the growth of GaAs crystals by the Floating Zone technique under microgravity	Crystal Properties and Preparation 35 (1991), p. 138

1991	G. Müller	InP – the basic material of integrated optoelectronics for fiber communication systems	Physica Scripta T35 (1991), p. 201
1991	F. Mosel, A. Seidl, D. Hofmann, G. Müller	Optical and electrical characterization of n- and p-type Fe-doped InP	J. Electron. Materials 20 (1991), p. 1091
1991	F. Mosel, A. Seidl, D. Hofmann, G. Müller	Infrared absorption of n- and p-type Fe-doped InP and mapping of the Fe distribution	Appl. Surf. Sci. 50 (1991), p. 364
1991	F. Mosel, A. Seidl, D. Hofmann, G. Müller	LEC-growth and characterization of n- and p-type Fe-doped InP	Third International Conference. Indium Phosphide and Related Materials (Cat. No.91CH2950-4) IEEE, New York, NY, USA, 1991, xxiv+678, p. 331
1991	P. Kipfer, J. Lindolf, D. Hofmann, G. Müller	Study of the influence of the phosphorus pressure on the preparation of nominally undoped semi-insulating InP wafers	J. Appl. Phys. 69 (1991), p. 3860
1991	G. Hirt, D. Hofmann, F. Mosel, N. Schäfer, G. Müller	Annealing and bulk crystal growth of undoped InP under controlled P-pressure: a perspective for the preparation of undoped SI InP	Third International Conference. Indium Phosphide and Related Materials (Cat. No.91CH2950-4) IEEE, New York, NY, USA, 1991, xxiv+678, p. 16
1991	G. Hirt, D. Hofmann, F. Mosel, N. Schäfer, G. Müller	Compensation mechanisms in normally undoped semi-insulating InP and comparison with undoped InP Grown under stoichiometry control	J. Electron. Materials 20 (1991), p. 1065
1991	J. Baumgartl, G. Müller	Untersuchungen zum Einfluß von verminderter Gravitation und statischer magnetischer Felder auf ein Zonenschmelzmodell	Forschung unter Weltraumbedingungen, DARA Symposium (1991), pp. 332-337
1990	W. Weber, G. Neumann, G. Müller	Stabilizing Influence of the Coriolis Force During Melt Growth on a Centrifuge	Journal of Crystal Growth 100 (1990), pp. 145-158
1990	B. Reppich, K. Rieger, G. Müller	Dynamische Verformung von InP-Einkristallen bei höchsten Temperaturen mittels Liquid-Encapsulation (LE)-Technik	Zeitschrift für Metallkunde 81 (1990), pp. 166-173
1990	G. Neumann	Three-dimensional numerical simulation of buoyancy driven convection in vertical cylinders heated from below	J. Fluid Mech 214 (1990), pp. 559-578
1990	G. Mueller, D. Hofmann, P. Kipfer, F. Mosel	The preparation of Fe-doped and nominally undoped semi-insulating InP	Second International Conference. Indium Phosphide and Related Materials (Cat. No.90CH2859-7). IEEE, New York, NY, USA, 1990, xiii+451, p. 21
1990	G. Müller	A Comparative Study of Crystal Growth Phenomena Under Reduced and Enhanced Gravity	Journal of Crystal Growth 99 (1990), pp. 1242-1257
1990	P. Kipfer, D. Hofmann, G. Müller, A. Schöner, G. Pensl	A comparative study of compensation mechanisms in nominally undoped s.i. InP and Fe-doped InP crystals	Proc. 6th Conf. On Semi-insulating III-V Materials, Toronto (1990), pp. 11-16
1990	J. Baumgartl, M. Gewalt, R. Rupp, J. Stierlein, G. Müller	The Use of Magnetic Fields and Microgravity in Melt Growth of Semiconductors: A Comparative Study	Proceedings VIth European Symposium on Materials and Fluid Sciences under Microgravity, ESA SP-295, pp. 47-58
1989	J. Vökl, G. Müller	A New Model for the Calculation of Dislocation Formation in Semiconductor Melt Growth by Taking into Account the Dynamics of Plastic Deformation	Journal of Crystal Growth 97 (1989), pp. 136-145
1989	H.-J. Sell, G. Müller	Numerical Modelling of the Growth and Composition of GaXIn1-XAs Bulk Mixed Crystals by the Travelling Heater Method	Journal of Crystal Growth 97 (1989), pp. 194-200

1989	R. Rupp, G. Müller, G. Neumann	Three-Dimensional Time Dependent Modelling of the Marangoni Convection on Zone Melting Configurations for GaAs	Journal of Crystal Growth 97 (1989), pp. 34-41
1989	D. Hofmann, G. Müller, N. Streckfuß	Semi-Insulating Electrical Properties of Undoped InP after Heat Treatment in a Phosphorus Atmosphere	Applied Physics A 48 (1989), pp. 315-319
1989	J. Baumgartl, W. Budweiser, G. Müller, G. Neumann	Studies of Buoyancy Driven Convection in a Vertical Cylinder with Parabolic Temperature Profile	Journal of Crystal Growth 97 (1989), pp. 9-17
1988	J. Völkl, G. Müller	Dynamical Model of Dislocation Formation During LEC-Growth of InP	Proceedings of the 5th Conference on Semi-Insulating III-V Materials (1988), pp. 489-494
1988	G. Müller, G. Neumann	Numerische Modellbildung bei der Kristallzüchtung aus Schmelzen	Forschung unter Schwerelosigkeit, BMFT-DFVLR Statusseminar (1988), pp. 145-150
1988	G. Müller	Convection and Inhomogenities	in Crystal Growth from the Melt, Springer-Verlag, Berlin, 1988
1988	D. Hofmann, F. Mosel, G. Müller	Influence of a Vertical Magnetic Field on the LEC-Growth and Properties of 3 inch s.i. InP-Crystals	Proceedings of the 5th Conference on Semi-Insulating III-V Materials (1988), pp. 429-434
1987	J. Völkl, G. Müller, W. Blum	Analysis of Generation and Movement of Dislocations in InP by a Study of the Deformation Behaviour	Journal of Crystal Growth, 83 (1987), pp. 383-390
1987	J. Völkl, G. Müller	Analysis of Thermally Induced Stress in the LEC Growth of InP Crystals	Proceedings of the European Materials Research Society Conference, XVI (1987), pp. 141-150
1987	G. Müller, G. Neumann, H. Matz	A Two-Rayleigh-Number Model of Buoyancy-Driven Convection in Vertical Melt Growth Configuration	Journal of Crystal Growth, 84 (1987), pp. 33-49
1987	G. Müller	Non-Uniformity of InP Substrate Crystals (invited)	Proceedings of the European Materials Research Society Conference, XVI (1987), pp. 117-130
1987	D.T.J. Hurle, G. Müller, R. Nitsche	Crystal growth from the melt	in Fluid Sciences and Material Science in Space (Editor H. Walter) Springer Berlin, 1987, pp. 313-354
1986	G. Müller, P. Kyr	Directional Solidification of the InSb-NiSb Eutectic	Proceedings of the Symposium on Scientific Results of the German Spacelab Mission D1 (1987), pp. 246-259
1986	G. Müller	Über die Entstehung von Inhomogenitäten in Halbleiterkristallen bei der Herstellung aus Schmelzen	Selisch Fachbuch Verlag, Erlangen, 1986
1985	G. Müller, R. Rupp, J. Völkl, H. Wolf, W. Blum	Deformation Behaviour and Dislocation Formation in Undoped and Doped (Zn, S) InP Crystals	Journal of Crystal Growth, 71 (1985), pp. 771-781
1984	G. Müller, G. Neumann, W. Weber	Natural Convection in Vertical Bridgman Configuration	Journal of Crystal Growth, 70 (1984), pp. 78-94
1984	G. Müller, P. Kyr	Directional Solidification of the InSb-NiSb Eutectic	Proceedings of the 5th European Symposium on Materials Sciences under Microgravity ESA SP-222 (1984), pp. 141-146

1983	F. Rosenberger, G. Müller	Interfacial Transport in Crystal Growth, a Parametric Comparison of Convective effects	Journal of Crystal Growth, 65 (1983), pp. 91-104
1983	G. Müller, J. Völkl, E. Tomzig	Thermal Analysis of LEC InP Growth	Journal of Crystal Growth, 64 (1983), pp. 40-47
1983	G. Müller	Convection in Melts and Crystal Growth	Adv. Space Res., 3 (1983), pp. 51-60
1983	G. Müller, J. Pfannenmüller, E. Tomzig, J. Völkl, F. Köhl	Sources of Silicon Contamination in LEC-Grown InP Crystals	Journal of Crystal Growth, 64 (1983), pp. 37-39
1983	G. Müller, G. Neumann	Tenfold Growth Rates in the Travelling Heater Method of GaSb Crystals by Forced Convection on a Centrifuge	Journal of Crystal Growth, 63 (1983), pp. 58-66
1983	G. Müller, G. Neumann	Investigation of Convective Flows in Model System of Directional Solidification Configurations	Proceedings of the 4th European Symposium on Materials Sciences under Microgravity ESA SP-191 (1983), pp. 285-294
1982	G. Müller	Convection in Melts and Crystal Growth	Convective Transport and Instability Phenomena (1982), pp. 441-467
1982	G. Müller, G. Neumann	Suppression of Doping Striations in Zone Melting of InSb by Enhanced Convection on a Centrifuge	Journal of Crystal Growth, 59 (1982), pp. 548-556
1982	P. Kyr, G. Müller	Entwicklung eines Experimentkonzepts zur gerichteten Erstarrung des InSb-NiSb Eutektikums im Weltraum	Zeitschrift für Flugwissenschaft und Weltraumforschung, 6 (1982), pp. 152-159
1982	A. Bewersdorff, G. Müller, H. Oerteljun., P.R. Sahm, H.J. Sell, J. Siekmann	Grenzflächen- und Transportphänomene unter Weltraumbedingungen, Teil I: Transportvorgänge	Zeitschrift für Flugwissenschaft und Weltraumforschung, 6 (1982), pp. 367-382
1981	G. Müller	Konvektive Transportvorgänge bei der Materialherstellung aus Schmelzen mit kleiner Prandtlzahl	Zeitschrift für Flugwissenschaften und Weltraumforschung, 5. Jahrg. (1981), pp. 1-8
1980	G. Müller	Konvektive Transportvorgänge in Metall und Halbleiterschmelzen	in Spacelab-Nutzung, DGLR Bericht 80-01 (1980), pp. 97-105
1980	G. Müller, E. Schmidt, P. Kyr	Investigation of Convection in Melts and Crystal Growth Under Large Inertial Accelerations	Journal of Crystal Growth, 49 (1980), pp. 387-395
1980	P. Kyr, G. Müller	Untersuchungen von Wachstumsparametern bei der gerichteten Erstarrung des InSb-NiSb Eutektikums	in Spacelab-Nutzung, DGLR Bericht 80-01 (1980), pp. 279-289
1979	K.W. Benz, G. Müller	High-quality III-V Semiconductor Substrate Crystals Grown by the Travelling-Heater Method (THM)	Gallium Arsenide and Related Compounds 1978. Inst. Physics, London, UK, 1979, xiii+533, pp. 154-162
1979	K.W. Benz, G. Müller	GaSb and InSb Crystals Grown by Vertical and Horizontal Travelling Heater Method	Journal of Crystal Growth, 46 (1979), pp. 35-42
1979	P. Kyr, G. Müller	Gerichtetes Erstarren des InSb-NiSb Eutektikums im Gradientenofen	in Spacelab-Nutzung, DGLR Bericht 79-01 (1979), pp. 161-169

1979	K. Benz, G. Müller, H. Weiß	Eigenschaften von GaSb Einkristallen mit der Lösungszone	in Spacelab-Nutzung, DGLR Bericht 79-01 (1979), pp. 123-130
1979	K.W. Benz, G. Müller	III-V-Semiconductor Crystals Grown by the Travelling-Heater Method	Proceedings of the 3rd European Symposium on Material Science in Space ESA SP-142 (1979), pp. 369-373
1976	G. Müller	Crystal Growth at Greater than 1g	Proceedings of 2nd European Symposium on "Material Science in Space", ESA Special Publication, 114 (1976), pp. 213-216